EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1309	(438/710).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 13:03
S2	6	(@ad<="20030826") and ((micromask$5) adj (residu$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:15
S3	7	(@ad<="20030826") and ((micromask$5) near (residu$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 09:37
S4	43	(@ad<="20030826") and ((micromask$5) same (residu$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 09:46
S5	6	(@ad<="20030826") and ((micromask$5) same (residu$4) same (reduc$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 09:38
S6	96147	(@ad<="20030826") and ((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 10:45
S7	3	(@ad<="20030826") and ((micromask$5) same (residu$4)) and (hardmask) and (ARC) and (plasma) and (etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 09:47
S8	600	(@ad<="20030826") and ((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes) and (arc) and (mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 10:46
S9	136	(@ad<="20030826") and ((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes) and (arc) and (mask) and (etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 10:49
S10	96121	(@ad<="20030826") and (arc) and (mask) and (etch) and ((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 10:54

S11	74	(@ad<="20030826") and (arc) and (mask) and (etch) and (((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:09
S12	1	(@ad<="20030826") and ((arc) near (metal$4)) and ((hardmask) near (oxide)) and (etch) and (((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:12
S13	0	(@ad<="20030826") and ((arc) near ((Ti) or (titanium))) and ((hardmask) near (oxide)) and (etch) and (((micromask$5) same (residu$4)) or ((cone) adj (defects)) or (spikes))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:13
S14	0	(@ad<="20030826") and ((arc) near ((Ti) or (titanium))) and ((hardmask) near (oxide)) and (etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:14
S15	10	(@ad<="20030826") and ((arc) same ((Ti) or (titanium))) and ((hardmask) near (oxide)) and (etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:18
S16	123	(@ad<="20030826") and (micromask$4) and (residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:14
S17	33	(@ad<="20030826") and (micromask$4) and (residu$3) and ((arc) or (Ti))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:21
S18	2034	(@ad<="20030826") and (residu$3) and ((arc) or (Ti)) and ((cl2) or ("cl.sub.2") or (hcl) or (bcl3) or ("bcl.sub.3")) and (etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/04 18:37
S19	1686	(@ad<="20030826") and (residu$3) and ((arc) or (Ti)) and ((cl2) or ("cl.sub.2") or (hcl) or (bcl3) or ("bcl.sub.3")) and (etch) and ((oxide) or (TEOS))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:24
S20	33	(@ad<="20030826") and (residu$3) and ((arc) same (Ti)) and ((cl2) or ("cl.sub.2") or (hcl) or (bcl3) or ("bcl.sub.3")) and (etch) and ((oxide) or (TEOS))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:25

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S21	29	(@ad<="20030826") and (438/710.ccls.) and (etch) and (arc) and (TEOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:15
S22	3	(@ad<="20030826") and (etch) and (arc) and (TEOS) and (residu$4) and (grass$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:17
S23	308	(@ad<="20030826") and (etch) and (arc) and (TEOS) and ((residu$4) or (grass$4) or (micromask$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:18
S24	129	(@ad<="20030826") and (etch) and (arc) and (TEOS) and ((residu$4) or (grass$4) or (micromask$4)) and (Ti)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:53
S25	2	("6103633").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 13:53
S26	1	"5888859".PN.	USPAT; USOCR	OR	ON	2005/11/09 13:54
S27	1	"5641382".PN.	USPAT; USOCR	OR	ON	2005/11/09 13:54
S28	1	"5413669".PN.	USPAT; USOCR	OR	ON	2005/11/09 14:04
S29	1	"5350488".PN.	USPAT; USOCR	OR	ON	2005/11/09 14:05
S30	1	"5238872".PN.	USPAT; USOCR	OR	ON	2005/11/09 14:37
S31	1	"5200361".PN.	USPAT; USOCR	OR	ON	2005/11/09 14:40
S32	1	"5888859".PN.	USPAT; USOCR	OR	ON	2005/11/09 14:40
S33	5265	(@ad<="20030826") and ((Ti) or (TiN)) and (etch$4) and ((cl2) or ("cl.sub.2") or (BCl3) or ("BCL.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:15
S34	2161	(@ad<="20030826") and ((Ti) or (TiN)) and (etch$4) and ((cl2) or ("cl.sub.2") or (BCl3) or ("BCL.sub.3")) and (residu$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:15

EAST Search History

S35	1991	(@ad<="20030826") and ((Ti) or (TiN)) and (etch$4) and ((cl2) or ("cl.sub.2") or (BCl3) or ("BCL.sub.3")) and (residu$4) and ((oxide) or (TEOS))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:16
S36	289	(@ad<="20030826") and ((Ti) or (TiN)) and (etch$4) and ((cl2) or ("cl.sub.2") or (BCl3) or ("BCL.sub.3")) and (residu$4) and ((oxide) or (TEOS)) and (arc)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:16
S37	265	(@ad<="20030826") and ((Ti) or (TiN)) and (etch$4) and ((cl2) or ("cl.sub.2") or (BCl3) or ("BCL.sub.3")) and (residu$4) and ((oxide) or (TEOS)) and (arc) and (plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:17
S38	2	(@ad<="20030826") and ("6,103,633")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 14:23
S39	787	(438/720).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/10 14:22
S40	757	(@ad<="20030826") and (438/720.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 14:23
S41	3	(@ad<="20030826") and (((hardmask) and (aluminum) and (etch)).ti.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:27
S42	216	(@ad<="20030826") and (((hardmask) and (aluminum etch)).ab.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:30
S43	0	(@ad<="20030826") and (((hardmask) and ("aluminum etch")).ab.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:31
S44	0	(@ad<="20030826") and ((hardmask) near ("aluminum etch"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:32

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EAST Search History

S45	4	(@ad<="20030826") and ((hardmask) same ("aluminum etch"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:43
S46	17	(@ad<="20030826") and ((hardmask) and ("aluminum etch"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 15:43
S47	0	(@ad<="20030826") and ((clening) near (metal$4) near (residu$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:04
S48	10	(@ad<="20030826") and ((cleaning) near (metal$4) near (residu$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:07
S49	475	(@ad<="20030826") and ((cleaning) same (metal$4) near (residu$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:07
S50	155	(@ad<="20030826") and ((cleaning) same (metal$4) near (residu$3)) and (plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:18
S51	0	(@ad<="20030826") and ((cleaning) same (metal$4) near (residu$3)) and (plasma) and ((cl2) or (BCl3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:19
S52	0	(@ad<="20030826") and ((cleaning) same ((metal$4) near (residu$3))) and (plasma) and ((cl2) or (BCl3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:20
S53	2	(@ad<="20030826") and ((cleaning) and ((metal$4) near (residu$3))) and (plasma) and ((cl2) or (BCl3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:39
S54	43	(@ad<="20030826") and (etch$4) and (plasma) and (cl2) and (HCl) and (BCl3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:54

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S55	21	(@ad<="20030826") and (etch$4) and (plasma) and ((cl2) same (HCl) same (BCl3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:23
S56	0	("(UEDA-YASUHIKO.in.)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 16:23
S57	34	(UEDA-YASUHIKO.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:44
S58	67	(ouchi-masahiko.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:15
S59	3	(ouchi-masahiko.in.) and (residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:11
S60	10	(@ad<="20030826") and (arc) and (hardmask) and ((interface) near (layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:09
S61	6	(@ad<="20030826") and (arc) and (hardmask) and ((sion) near (layer)) and (residu$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:27
S62	28	(@ad<="20030826") and (arc) and (hardmask) and ((sion) or (oxinitride)) and (residu$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:41
S63	51	(@ad<="20030826") and (arc) and (hardmask) and ((sion) or (oxynitride)) and (residu$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:41
S64	2	("6103633").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 08:34

S65	2	(@ad<="20030826") and (arc) and (hardmask) and ("PE-TEOS")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:10
S66	2	(@ad<="20030826") and (arc) and (hardmask) and ("PE TEOS")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:10
S67	15	(@ad<="20030826") and (arc) and (hardmask) and ("PETEOS")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:10
S68	2	("20040157444").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/25 09:54
S69	920	(@ad<="20030826") and (residu$3) and (((arc) or (Ti)) with oxide) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 13:37
S70	561	(@ad<="20030826") and (residu$3) and (((arc) or (Ti)) with oxide) and etch and clean$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 09:30
S71	83	(@ad<="20030826") and (residu$3) and ((arc) with oxide) and etch and clean$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 09:32
S72	8	(@ad<="20030826") and ((residu$3) same (HCl)) and ((arc) with oxide) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 15:54
S73	394	(@ad<="20030826") and (134/1.2.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:13
S74	0	(@ad<="20030826") and (134/1.2.ccls.) and ((cholrine or hcl or cl or "cl.sub.2") with residu) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:14

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S75	0	(@ad<="20030826") and (134/1.2.ccls.) and (cholrine or hcl or cl or "cl.sub.2") and residu and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:15
S76	0	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and residu and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:15
S77	0	(@ad<="20030826") and (134/1.3.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and residu and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:16
S78	0	(@ad<="20030826") and (134/1.1.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and residu and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:16
S79	0	(@ad<="20030826") and (134/26.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and residu and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:16
S80	172	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine or hcl or cl or "cl.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:16
S81	160	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:17
S82	142	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and plasma and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:17
S83	101	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine or hcl or cl or "cl.sub.2") and plasma and substrate and residu$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:23
S84	49	(@ad<="20030826") and (134/1.2.ccls.) and ((chlorine or hcl or cl or "cl.sub.2") with plasma) and plasma and substrate and residu$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:24

EAST Search History

S85	49	(@ad<="20030826") and (134/1.2.ccls.) and ((chlorine or hcl or cl or "cl.sub.2") with plasma) and substrate and residu$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 14:35
S86	54	(@ad<="20030826") and (134/1.2.ccls.) and ((chlorine or hcl or cl or "cl.sub.2") with plasma) and residu$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:04
S87	5	(@ad<="20030826") and (134/1.2.ccls.) and (chlorine with (Ar or argon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:08
S88	0	(@ad<="20030826") and (134/1.2.ccls.) and ((chlorine with (Ar or argon)) same residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:09
S89	3	(@ad<="20030826") and ("134"/$4.ccls.) and ((chlorine with (Ar or argon)) same residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:10
S90	307	(@ad<="20030826") and ((chlorine with (Ar or argon)) same residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:10
S91	101	(@ad<="20030826") and ((chlorine with (Ar or argon)) same residu$3) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:13
S92	34	(@ad<="20030826") and ((chlorine with (Ar or argon)) same residu$3) and plasma and residu$3.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 16:15
S93	34	(@ad<="20030826") and plasma and residu$3.ab. and ((chlorine with (Ar or argon)) same residu$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 17:15
S94	5	(@ad<="20030826") and plasma and residu$3.ab. and ("2 mt" or "15 mt")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/05 17:18

S95	31	(@ad<="20030826") and plasma and residu$3.ab. and ("2 mt" or "15 mt" or "3 mt" or "5 mt" or "10 mt")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 07:11
S96	2	("20040157444").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/07 16:52
S97	32	(@ad<="20030826") and plasma and residu$3.ab. and (nodule or micromasking) and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 07:22
S98	51	(@ad<="20030826") and plasma and residu$3.ab. and (nodule or micromasking)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 07:22
S99	17	(@ad<="20030826") and plasma and residu$3.ab. and (nodule or micromasking) and (oxide or ARC)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 08:10
S100	17	(@ad<="20030826") and plasma and residu$3.ab. and (oxide adj (mask or hardmask or "hard mask")) and (ARC or antireflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 08:12
S101	2	("6103633").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/10 14:42
S102	32	(@ad<="20030826") and ((residu$3) same (HCl or cl chlorine or cl2 or "cl.sub.2")) and ((arc) with oxide) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 06:38
S103	308	(@ad<="20030826") and ((residu$3) same (HCl or cl chlorine or cl2 or "cl.sub.2")) and ((Ti or titanium) with oxide) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 06:39
S104	147	(@ad<="20030826") and ((residu$3 with remov$4) same (HCl or cl chlorine or cl2 or "cl.sub.2")) and ((Ti or titanium) with oxide) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 06:40

EAST Search History

S10 5	19	(@ad<="20030826") and ((residu$3 with remov$4) same (HCl or cl chlorine or cl2 or "cl.sub.2") same ((Ti or titanium) with oxide)) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 07:00
S10 6	1	(@ad<="20030826") and ((residu$3 with micromask$4) same (HCl or cl chlorine or cl2 or "cl.sub.2") same ((Ti or titanium) with oxide)) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 07:01
S10 7	1	(@ad<="20030826") and ((micromask$4) same (HCl or cl chlorine or cl2 or "cl.sub.2") same ((Ti or titanium) with oxide)) and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 07:01

Inventor Name Search Result

Your Search was:

Last Name = TANG
First Name = WOODY

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10649099	Not Issued	71	08/26/2003	Methods of reducing or removing micromasking residue prior to metal etch using oxide hardmask	TANG, WOODY K. SATTAYAPIWAT

Inventor Search Completed: No Records to Display.

	Last Name	First Name	
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Inventor Name Search Result

Your Search was:

Last Name = KOVALL
First Name = GEORGE

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10821100	Not Issued	83	04/07/2004	Method of forming ONO-type sidewall with reduced bird's beak	KOVALL, GEORGE
10402745	Not Issued	41	03/28/2003	Method for etching a titanium-containing layer prior to etching an aluminum layer in a metal stack	KOVALL, GEORGE A.
10649099	Not Issued	71	08/26/2003	Methods of reducing or removing micromasking residue prior to metal etch using oxide hardmask	KOVALL, GEORGE A.
10718320	Not Issued	71	11/19/2003	Dynamically controllable reduction of vertical contact diameter through adjustment of etch mask stack for dielectric etch	KOVALL, GEORGE A.
07797351	Not Issued	166	11/25/1991	PLASMA APPARATUS INCLUDING SPUTTERING ELECTRODE FOR CLEANING DIELECTRIC WINDOW OF PLASMA CHAMBER AND METHOD OF SPUTTER CLEANING DIELECTRIC WINDOW OF PLASMA CHAMBER	KOVALL, GEORGE A.
08056873	Not Issued	161	05/05/1993	PLASMA APPARATUS INCLUDING SPUTTERING ELECTRODE FOR CLEANING DIELECTRIC WINDOW OF PLASMA CHAMBER AND METHOD OF SPUTTER CLEANING DIELECTRIC WINDOW OF PLASMA CHAMBER	KOVALL, GEORGE A.

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Inventor Name Search Result

Your Search was:

Last Name = DING
First Name = YI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09014388	5932991	150	01/28/1998	SYSTEM AND METHOD FOR BATTERY CHARGING WITH ACOUSTIC EXCITATION	DING, YI
09165944	6094033	150	10/02/1998	BATTERY STATE OF CHARGE DETECTOR WITH RAPID CHARGING CAPABILITY AND METHOD	DING, YI
09410195	6374003	150	09/30/1999	METHOD AND APPARATUS FOR OPTICALLY MODULATING LIGHT THROUGH THE BACK SIDE OF AN INTEGRATED CIRCUIT DIE USING A PLURALITY OF OPTICAL BEAMS	DING, YI
09434866	6480641	150	11/04/1999	METHOD AND APPARATUS FOR OPTICALLY MODULATING LIGHT THROUGH THE BACK SIDE OF AN INTEGRATED CIRCUIT DIE ALONG THE SIDE WALLS OF JUNCTIONS	DING, YI
09471936	6351576	150	12/23/1999	OPTICAL CLOCKING DISTRIBUTION USING DIFFRACTIVE METAL MIRRORS AND METAL VIA WAVEGUIDES	DING, YI
09543275	6229285	150	04/05/2000	Detector for rapid charging and method	DING, YI
09676293	6449405	150	09/28/2000	METHOD AND APPARATUS FOR SWITCHING A PLURALITY OF OPTICAL BEAMS IN AN OPTICAL SWITCH	DING, YI
09676294	6434289	150	09/28/2000	METHOD AND APPARATUS	DING, YI

				FOR CONFINING AN OPTICAL BEAM IN AN OPTICAL SWITCH	
09676297	6421473	150	09/28/2000	METHOD AND APPARATUS FOR SWITCHING AN OPTICAL BEAM IN AN INTEGRATED CIRCUIT DIE	DING, YI
09761285	6580977	150	01/16/2001	HIGH EFFICIENCY FUEL CELL AND BATTERY FOR A HYBRID POWERTRAIN	DING, YI
09811171	6690036	150	03/16/2001	METHOD AND APPARATUS FOR STEERING AN OPTICAL BEAM IN A SEMICONDUCTOR SUBSTRATE	DING, YI
09823694	6441676	150	03/30/2001	EXTERNALLY PROGRAMMABLE ANTIFUSE	DING, YI
09848397	6733909	150	05/03/2001	FUEL CELL POWER PLANT WITH ELECTROCHEMICAL ENHANCED CARBON MONOXIDE REMOVAL	DING, YI
09861450	6632555	150	05/18/2001	PROTON ELECTROLYTE MEMBRANE FUEL CELL WITH ANTI-FREEZE COOLANT AND HUMIDIFIERS	DING, YI
10040581	Not Issued	161	12/28/2001	Test fixture for die-level testing of planar lightwave circuits	DING, YI
10063195	6744237	150	03/28/2002	HYBRID POWER SYSTEM FOR AN ELECTRIC VEHICLE	DING, YI
10167802	6888398	150	06/11/2002	EXTERNALLY PROGRAMMABLE ANTIFUSE	DING, YI
10177872	6891653	150	06/19/2002	METHOD AND APPARATUS FOR STEERING AN OPTICAL BEAM IN A SEMICONDUCTOR SUBSTRATE	DING, YI
10252143	7005338	150	09/19/2002	NONVOLATILE MEMORY CELL WITH A FLOATING GATE AT LEAST PARTIALLY LOCATED IN A TRENCH IN A SEMICONDUCTOR SUBSTRATE	DING, YI
10262785	6743675	150	10/01/2002	FLOATING GATE MEMORY FABRICATION METHODS COMPRISING A FIELD DIELECTRIC ETCH WITH A HORIZONTAL ETCH COMPONENT	DING, YI

10367268	6928209	150	02/15/2003	OPTICAL ADD AND DROP MULTIPLEXER USING RING RESONATORS	DING, YI
10386924	6805972	150	03/13/2003	METHOD OF FORMING NANOPOROUS MEMBRANES	DING, YI
10393202	6995060	150	03/19/2003	FABRICATION OF INTEGRATED CIRCUIT ELEMENTS IN STRUCTURES WITH PROTRUDING FEATURES	DING, YI
10393212	6962851	150	03/19/2003	NONVOLATILE MEMORIES AND METHODS OF FABRICATION	DING, YI
10408598	Not Issued	123	04/07/2003	Arrayed waveguide grating based power monitor	DING, YI
10411813	6893921	150	04/10/2003	NONVOLATILE MEMORIES WITH A FLOATING GATE HAVING AN UPWARD PROTRUSION	DING, YI
10430559	Not Issued	161	05/06/2003	Hybrid optical circuits with thin film filters	DING, YI
10440005	6974739	150	05/16/2003	FABRICATION OF DIELECTRIC ON A GATE SURFACE TO INSULATE THE GATE FROM ANOTHER ELEMENT OF AN INTEGRATED CIRCUIT	DING, YI
10440466	6902974	150	05/16/2003	FABRICATION OF CONDUCTIVE GATES FOR NONVOLATILE MEMORIES FROM LAYERS WITH PROTRUDING PORTIONS	DING, YI
10440500	Not Issued	71	05/16/2003	Methods Of Fabricating Integrated Circuits With Openings That Allow Electrical Contact To Conductive Features Having Self-Aligned Edges	DING, YI
10440508	6846712	150	05/16/2003	FABRICATION OF GATE DIELECTRIC IN NONVOLATILE MEMORIES HAVING SELECT, FLOATING AND CONTROL GATES	DING, YI
10455852	Not Issued	161	06/06/2003	Double sided optoelectronic integrated circuit	DING, YI
10608726	Not Issued	161	06/27/2003	Measuring coupling characteristics of optical devices	DING, YI
10631452	7060565	150	07/30/2003	FABRICATION OF DIELECTRIC	DING, YI

				FOR A NONVOLATILE MEMORY CELL HAVING MULTIPLE FLOATING GATES	
10631552	6962852	150	07/30/2003	NONVOLATILE MEMORIES AND METHODS OF FABRICATION	DING, YI
10631941	Not Issued	95	07/30/2003	NONVOLATILE MEMORY CELL WITH MULTIPLE FLOATING GATES FORMED AFTER THE SELECT GATE	DING, YI
10632007	6885044	150	07/30/2003	ARRAYS OF NONVOLATILE MEMORY CELLS WHEREIN EACH CELL HAS TWO CONDUCTIVE FLOATING GATES	DING, YI
10632154	7052947	150	07/30/2003	FABRICATION OF GATE DIELECTRIC IN NONVOLATILE MEMORIES IN WHICH A MEMORY CELL HAS MULTIPLE FLOATING GATES	DING, YI
10632155	7101757	150	07/30/2003	NONVOLATILE MEMORY CELLS WITH BURIED CHANNEL TRANSISTORS	DING, YI
10632186	6951782	150	07/30/2003	NONVOLATILE MEMORY CELL WITH MULTIPLE FLOATING GATES FORMED AFTER THE SELECT GATE AND HAVING UPWARD PROTRUSIONS	DING, YI
10644585	Not Issued	160	08/20/2003	Proton electrolyte membrane fuel cell with anti-freeze coolant and humidifiers	DING, YI
10647436	Not Issued	41	08/26/2003	Method of plating metal leafs and metal membranes	DING, YI
10649099	Not Issued	71	08/26/2003	Methods of reducing or removing micromasking residue prior to metal etch using oxide hardmask	DING, YI
10678317	6838342	150	10/03/2003	NONVOLATILE MEMORY FABRICATION METHODS COMPRISING LATERAL RECESSING OF DIELECTRIC SIDEWALLS AT SUBSTRATE ISOLATION REGIONS	DING, YI
10702813	Not Issued	41	11/06/2003	System and method for charging a battery	DING, YI
10797972	Not	95	03/10/2004	FABRICATION OF	DING, YI

	Issued			CONDUCTIVE LINES INTERCONNECTING FIRST CONDUCTIVE GATES IN NONVOLATILE MEMORIES HAVING SECOND CONDUCTIVE GATES PROVIDED BY CONDUCTIVE GATE LINES, WHEREIN THE ADJACENT CONDUCTIVE GATE LINES FOR THE ADJACENT COLUMNS ARE SPACED FROM EACH OTHER, AND NON-	
10798475	Not Issued	41	03/10/2004	Fabrication of conductive lines interconnecting conductive gates in nonvolatile memories, and non-volatile memory structures	DING, YI
10803599	6844586	150	03/17/2004	FABRICATION OF GATE DIELECTRIC IN NONVOLATILE MEMORIES HAVING SELECT, FLOATING AND CONTROL GATES	DING, YI
10847850	7057231	150	05/17/2004	NONVOLATILE MEMORY CELL WITH A FLOATING GATE AT LEAST PARTIALLY LOCATED IN A TRENCH IN A SEMICONDUCTOR SUBSTRATE	DING, YI
10848924	7027677	150	05/19/2004	INTEGRATING OPTICAL COMPONENTS ON A PLANAR LIGHT CIRCUIT	DING, YI

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